



DCR2770A85

Phase Control Thyristor

Replaces DS6360-1 DS6360-2 March 2022 (LN41631)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Crowbar
- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to 125°C,
DCR2770A85*	8500	IDRM = IRRM = 300mA,
DCR2770A80	8000	VDRM, VRRM tp = 10ms
DCR2770A75	7500	VDSM & VRSM =
DCR2770A70	7000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

KEY PARAMETERS

V DRM	8500V
I _{T(AV)}	2770A
Ітѕм	36600A
dV/dt*	1500V/µs
dl/dt	200A/μs

^{*} Higher dV/dt selections are available on request

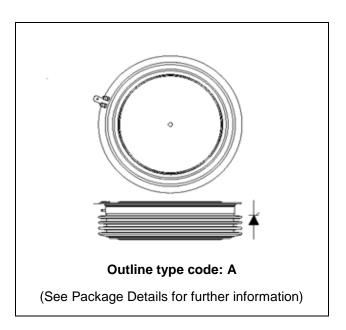


Fig. 1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR2770A85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

www.dynexsemi.com 1/10

^{*8200}V @ -40°C, 8500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
İT(AV)	Mean on-state current	Half wave resistive load	2770	А
IT(RMS)	RMS value	-		Α
lτ	Continuous (direct) on-state current	-	4060	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	36.6	kA
l²t	I ² t for fusing	V _R = 0	6.70	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
		Double side cooled	DC	-	6.0	°C/kW
Rth(j-c)	Thermal resistance - junction to case	Cingle side and a	Anode DC	-	10.4	°C/kW
		Single side cooled	Cathode DC	-	14.9	°C/kW
D. C.	The second secon	Clamping force 83kN	Double side	-	1.0	°C/kW
Rth(c-h)	Thermal resistance - case to heatsink	nermal resistance - case to heatsink (with mounting compound)	Single side	-	2.0	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			74	91	kN

www.dynexsemi.com 2/10



DYNAMIC CHARACTERISTICS

Symbol Parameter		Test Conditions	Тур.	Max.	Units
1/1	Dook rovered and off state overent	At VRRM/VDRM, Tcase = 125°C		300	mA
IRRM/IDRM	Peak reverse and off-state current	At 50% VRRM/VDRM, Tcase = 125°C		-	mA

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		2.35	2.65	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , Tj = 125°C, g	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	100	A/µs
ui/ut	Trate of fise of off-state current	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	200	A/µs
V	Threshold voltage - Low level	500A to 3000A at Tcase = 1	25°C	-	1.09	V
V T(TO)	Threshold voltage - High level	3000A to 9000A at Tcase = 125°C		-	1.27	V
	On-state slope resistance - Low level	500A to 3000A at Tcase = 125°C		-	0.40	mΩ
ľτ	On-state slope resistance - High level	3000A to 9000A at Tcase = 125°C		-	0.34	mΩ
tgd	Delay time	$V_D = 67\%$ V_{DRM} , gate source 30V, 10Ω $t_T = 0.5 \mu s$, $T_J = 25 ^{\circ} C$		-	3	μs
tq	Turn-off time	IT = 3000A, Tj = 125°C, VR = 200V, dl/dt = 1A/µs, dVpR/dt = 20V/µs linear		-	1000	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dl/dt = 1A/μs		7240	11760	μC
Irr	Reverse recovery current	$V_R \sim 3400V$, $C_S = 1.5 \mu F$, $R_S = 63 \Omega$		68	87	А
lι	Latching current	Tj = 25°C, VD = 5V		-	3	Α
Ін	Holding current	Tj = 25°C, Rg-κ = ∞, Iτм = 50	0Α, Iτ = 5Α	-	300	mA

www.dynexsemi.com 3/10



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	٧
V GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Ідт	Gate trigger current	VDRM = 5V, Tcase = 25°C	400	mA
lgp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

CURVES

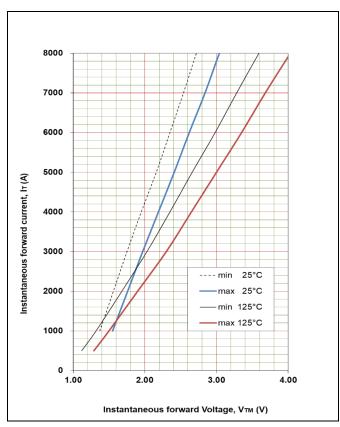


Fig. 2 Maximum & minimum on-state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = -0.067682

B = 0.214647

C = 0.000363

D = -0.008115

These values are valid for T_j = 125°C for I_T 500A to 9000A

www.dynexsemi.com 4/10



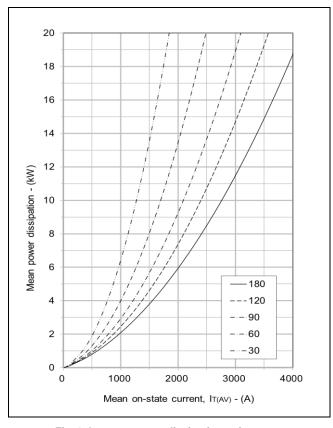


Fig. 3 On-state power dissipation - sine wave

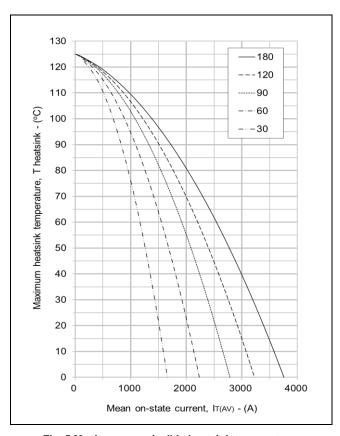


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

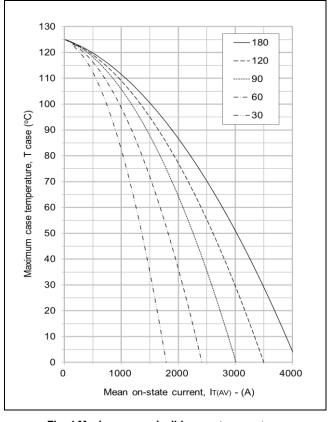


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

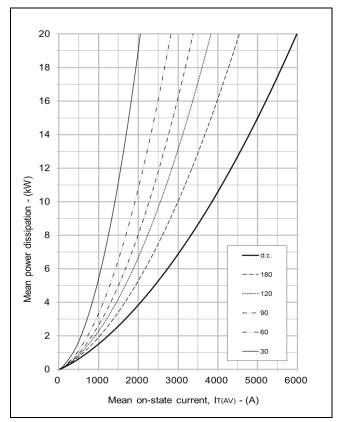


Fig. 6 On-state power dissipation - rectangular wave

www.dynexsemi.com 5/10



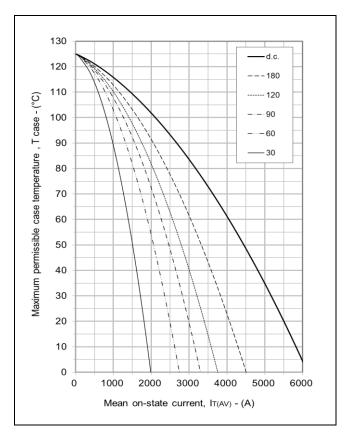
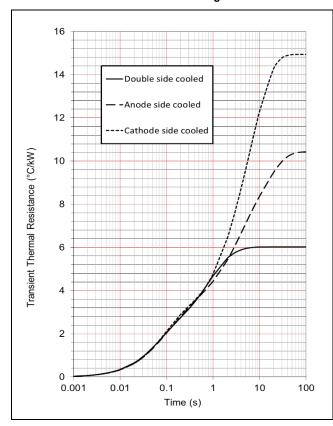


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



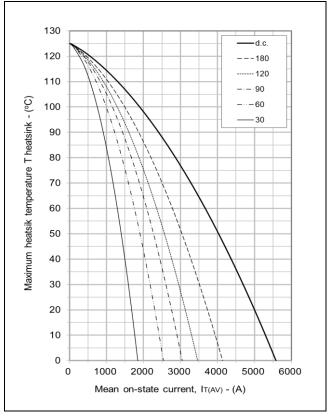


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	3.015	1.049	0.984	0.984
cooled	Ti(s)	0.704	1.905	0.059	0.059
Anode side cooled	Ri(°C/kW)	3.156	4.093	1.557	1.624
	Ti(s)	2.690	13.792	0.059	0.206
Cathode side	Ri(°C/kW)	7.077	3.483	1.746	2.634
cooled	Ti(s)	6.649	8.436	1.762	0.081

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}(j-c)}$ when the device operates at conduction angles other than d.c.

D	Double side cooling			
	ΔZ_{th}	(z)		
θ°	sine. rect.			
180	0.44	0.31		
120	0.49	0.43		
90	0.55	0.49		
60	0.60	0.55		
30	0.64	0.61		
15	0.66	0.64		

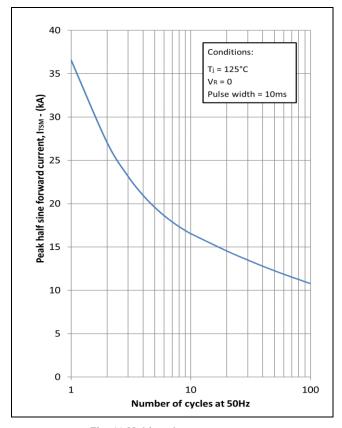
Ar	node Side Cooling		
	ΔZ_t	_h (z)	
θ°	sine.	rect.	
180	0.42	0.30	
120	0.47	0.41	
90	0.52	0.46	
60	0.57	0.52	
30	0.61	0.58	
15	0.62	0.61	

Cathode Sided Cooling			
	ΔZ	th (z)	
θ°	sine. rect.		
180	0.42	0.30	
120	0.47	0.41	
90	0.52	0.46	
60	0.57	0.52	
30	0.60	0.58	
15	0.62	0.60	

Fig.9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

www.dynexsemi.com 6/10





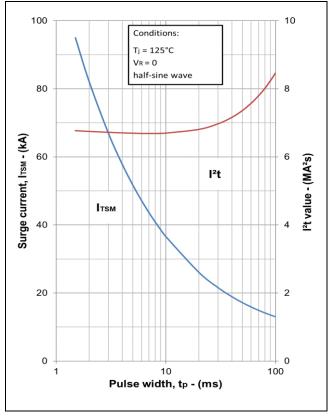


Fig. 10 Multi-cycle surge current

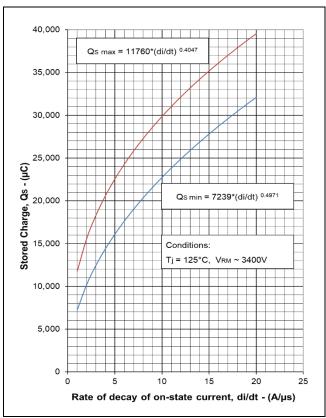


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

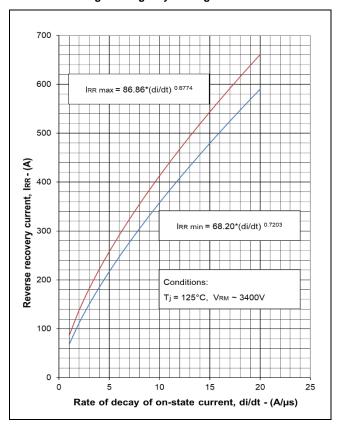


Fig. 13 Reverse recovery current

www.dynexsemi.com 7/10



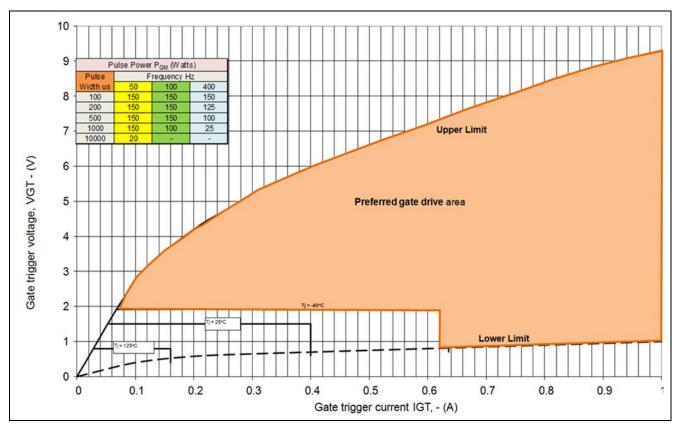


Fig.14 Gate characteristics

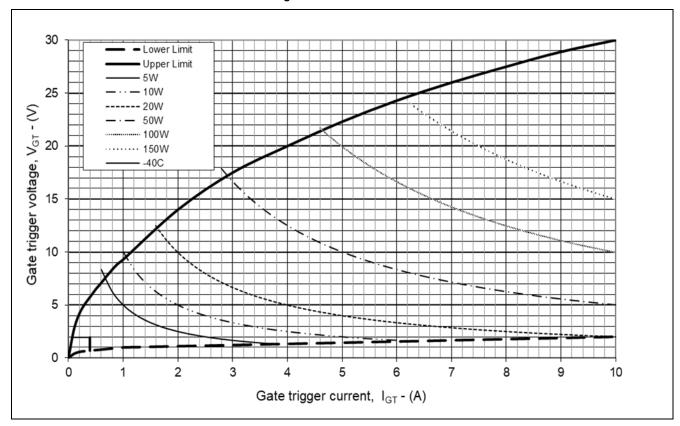


Fig. 15 Gate characteristics

www.dynexsemi.com 8/10



PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

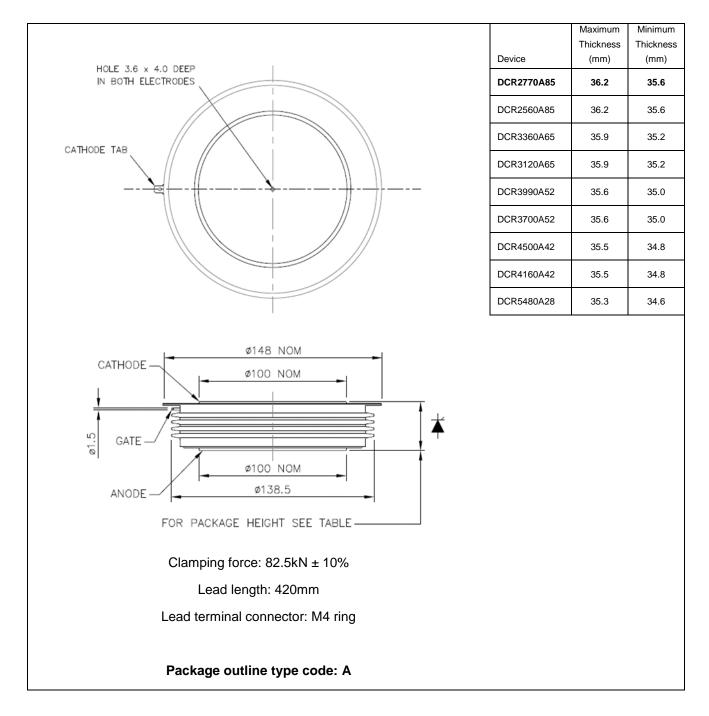


Fig. 16 Package outline

www.dynexsemi.com 9/10



IMPORTANT INFORMATION:

This publication is provided for information only and not for resale.

The products and information in this publication are intended for use by appropriately trained technical personnel.

Due to the diversity of product applications, the information contained herein is provided as a general guide only and does not constitute any guarantee of suitability for use in a specific application. The user must evaluate the suitability of the product and the completeness of the product data for the application. The user is responsible for product selection and ensuring all safety and any warning requirements are met. Should additional product information be needed please contact Customer Service.

Although we have endeavoured to carefully compile the information in this publication it may contain inaccuracies or typographical errors. The information is provided without any warranty or guarantee of any kind.

This publication is an uncontrolled document and is subject to change without notice. When referring to it please ensure that it is the most up to date version and has not been superseded.

The products are not intended for use in applications where a failure or malfunction may cause loss of life, injury or damage to property. The user must ensure that appropriate safety precautions are taken to prevent or mitigate the consequences of a product failure or malfunction.

The products must not be touched when operating because there is a danger of electrocution or severe burning. Always use protective safety equipment such as appropriate shields for the product and wear safety glasses. Even when disconnected any electric charge remaining in the product must be discharged and allowed to cool before safe handling using protective gloves.

Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

Product Status & Product Ordering:

We annotate datasheets in the top right hand corner of the front page, to indicate product status if it is not yet fully approved for production. The annotations are as follows:

Target Information: This is the most tentative form of information and represents a very preliminary specification.

No actual design work on the product has been started.

Provisional Information: Some initial development work has been performed. The datasheet represents a view of the

end product based on very limited information. Certain details will change.

Preliminary Information: The product design is complete and final characterisation for volume production is in progress.

The datasheet represents the product as it is now understood but details may change.

No Annotation: The product has been approved for production and unless otherwise notified by Dynex any

product ordered will be supplied to the current version of the data sheet prevailing at the

time of our order acknowledgement.

All products and materials are sold and services provided subject to Dynex's conditions of sale, which are available on request.

Any brand names and product names used in this publication are trademarks, registered trademarks or trade names of their respective owners.

HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire. LN6 3LF United Kingdom.

Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901

e-mail: powersolutions@dynexsemi.com

© Dynex Semiconductor Ltd. Technical Documentation – Not for resale.

www.dynexsemi.com 10/10